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# P-Channel 60 V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)			
- 60	$0.045 \text{ at V}_{GS} = -10 \text{ V}$	- 40 <sup>d</sup>			
	0.054 at V <sub>GS</sub> = - 4.5 V	- 40 <sup>d</sup>			

## **FEATURES**

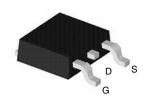
- DT-Trench Power MOSFET
- Material categorization:



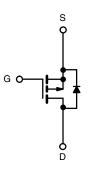
### **APPLICATIONS**

· Load Switch

# TO-252 Pin Configuration



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V <sub>DS</sub>	- 60	V			
Gate-Source Voltage	V <sub>GS</sub>	± 20	]			
Continuous Drain Current (T <sub>.1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	. I <sub>D</sub>	- 40 <sup>d</sup>	A		
Continuous Diam Guitent (1) = 173 C)	T <sub>C</sub> = 125 °C		- 27.5			
Pulsed Drain Current	I <sub>DM</sub>	- 110	1 ^			
Avalanche Current	I <sub>AS</sub>	- 30	]			
Single Pulse Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ		
Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	113 <sup>c</sup>	W		
Power Dissipation	T <sub>A</sub> = 25 °C	' D	2.5 <sup>b, c</sup>			
Operating Junction and Storage Temperature Range	·	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Junction-to-Ambient <sup>b</sup>	t ≤ 10 s	- R <sub>thJA</sub>	15	18	°C/W	
Junction-to-Ambient	Steady State		40	50		
Junction-to-Case		$R_{thJC}$	0.82	1.1		

### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Package limited.



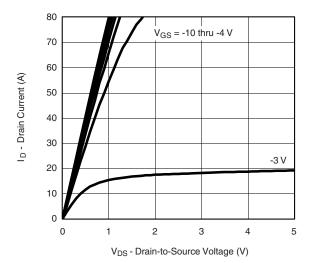
Parameter Symbol		Test Conditions		Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage		$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	$I_{GSS}$ $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA		
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V			- 1	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			- 50		
		V <sub>DS</sub> = - 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			- 100		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 10 V	- 50			Α	
		V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 5 A		0.045 0.055			
D : 0	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 125 °C			0.065	0	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 10 A, T <sub>J</sub> = 150 °C			0.073	0.073	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 5 A		0.054	0.069		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 17 A		61		S	
Dynamic <sup>b</sup>				-	•		
Input Capacitance	C <sub>iss</sub>			4950			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		480		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			405			
Total Gate Charge <sup>c</sup>	$Q_g$			110	165		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -40 \text{ A}$		19		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	]		28			
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			15	23		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = - 30 V, $R_L$ = 0.6 $\Omega$		70	105		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong -40 \text{ A}, V_{GEN} = -10 \text{ V}, R_G = 6$		175	260	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>	Ω		175	260	1	
Source-Drain Diode Ratings and Cha	racteristics -	T <sub>C</sub> = 25 °C <sup>b</sup>		•			
Continuous Current	I <sub>S</sub>				- 40	٨	
Pulsed Current	I <sub>SM</sub>				- 80	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 40 A, V <sub>GS</sub> = 0 V		- 1	- 1.6	V	
Reverse Recovery Time t <sub>rr</sub> I <sub>F</sub>		I <sub>F</sub> = - 40 A, dI/dt = 100 A/μs		45	70	ns	

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

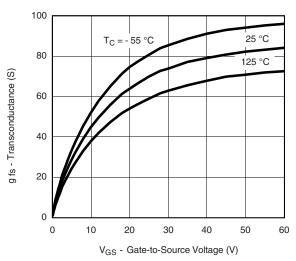
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



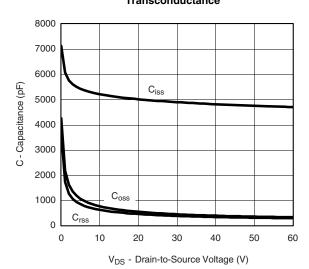
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



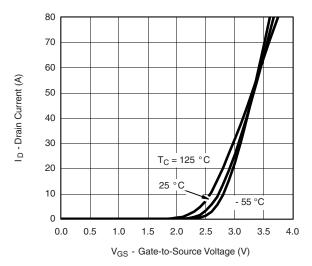
### **Output Characteristics**



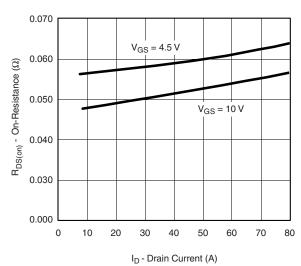
# Transconductance



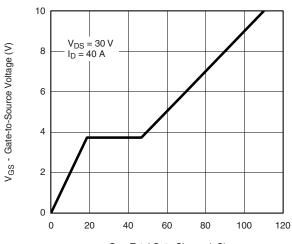
Capacitance



#### Transfer Characteristics



### On-Resistance vs. Drain Current

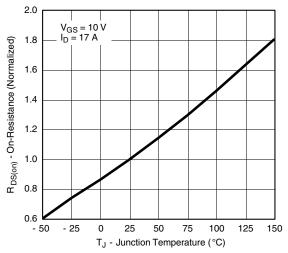


 $\mathbf{Q}_{\mathbf{g}}$  - Total Gate Charge (nC)

**Gate Charge** 

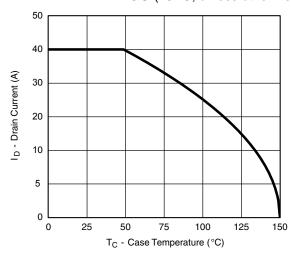


### **TYPICAL CHARACTERISTICS**

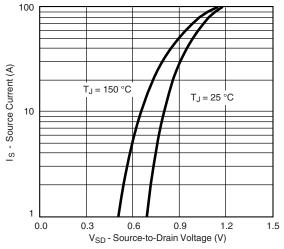


On-Resistance vs. Junction Temperature

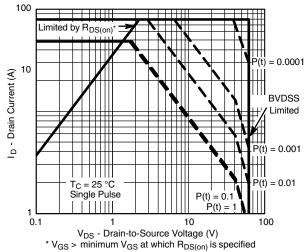
## THERMAL RATINGS (25 °C, unless otherwise noted)



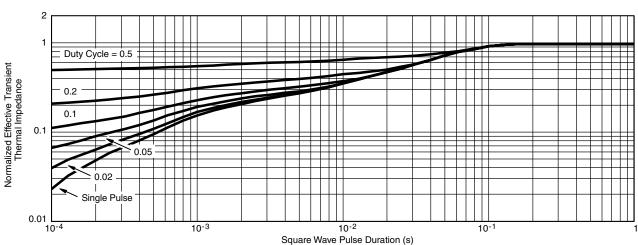
**Drain Current vs. Case Temperature** 



Source-Drain Diode Forward Voltage

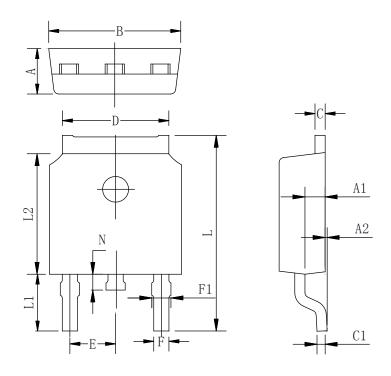


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

# **TO-252-2L PACKAGE OUTLINE**



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	
A	2.10	2.30	2.50	
A1	0.88	1.01	1.16	
A2	0.00	0.15	0.28	
В	6.40	6.60	6.80	
С	0.42	0.50	0.63	
C1	0.42	0.50	0.63	
D	5.08	5.32	5.65	
Е	2.286 TYP			
F	0.63	0.76	0.89	
F1	0.64	0.86	1.08	
L	9.30	9.90	10.80	
L1	2.4	2.8	3.6	
L2	5.90	6.10	6.55	
N	0.57	0.80	1.05	





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